

Key Issues in Plasma Processing

at present
wafer state
chamber condition



- etch rates
- particle test
- function tests (electrical)
- yield

in the future
process state
wafer state
chamber condition



- in-situ measurement
- monitoring
- fault detection
- run to run control



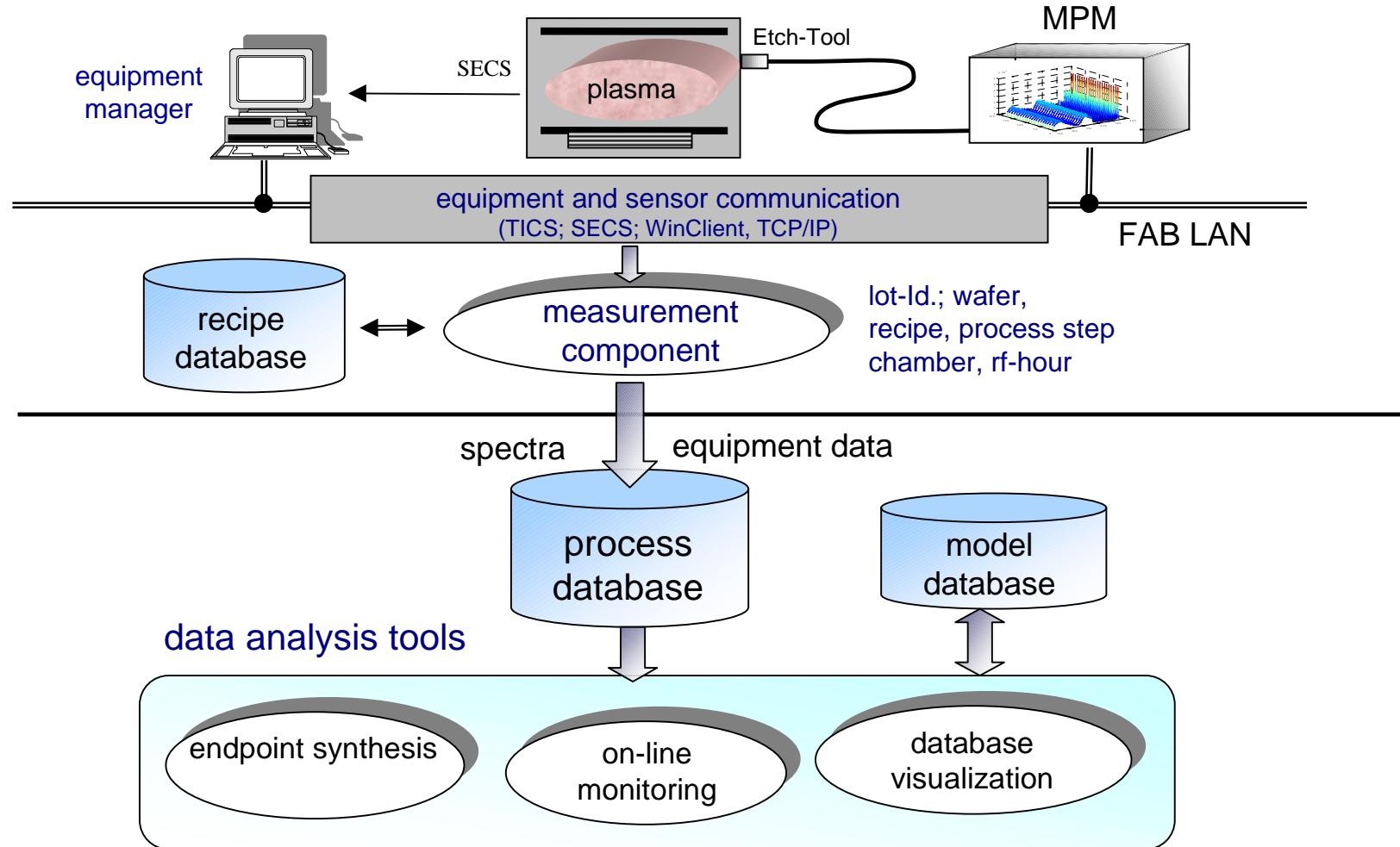
- Lack of diagnostic sensors at plasma processing tools
- Lack of standard sensor interfaces

Objectives

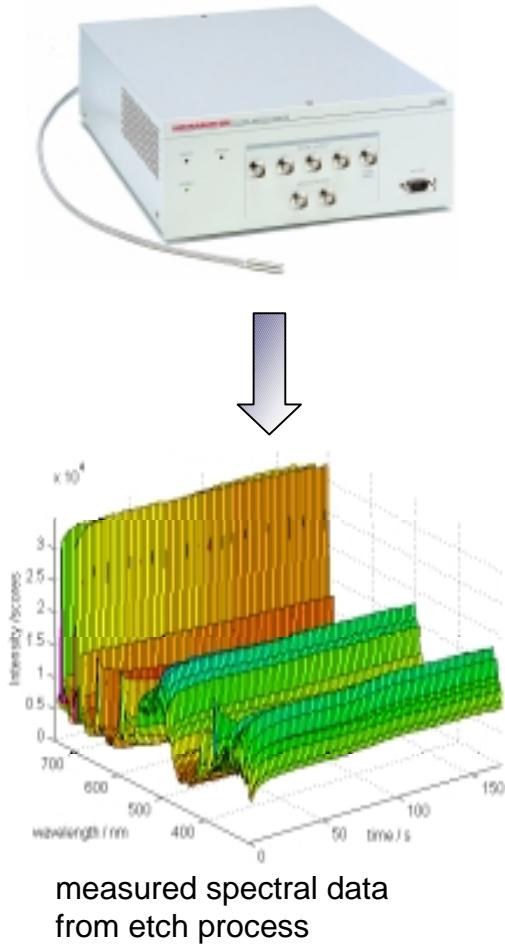
- Integration of Optical Emission Spectroscopy in industrial environment for in-situ process and equipment control
- Development and evaluation of advanced mathematical methods for long-term process monitoring, screening and diagnosis
- Synthesis of advanced endpoint signals and detection methods using whole spectral information



Integration of Hamamatsu MPM



Features of Hamamatsu MPM



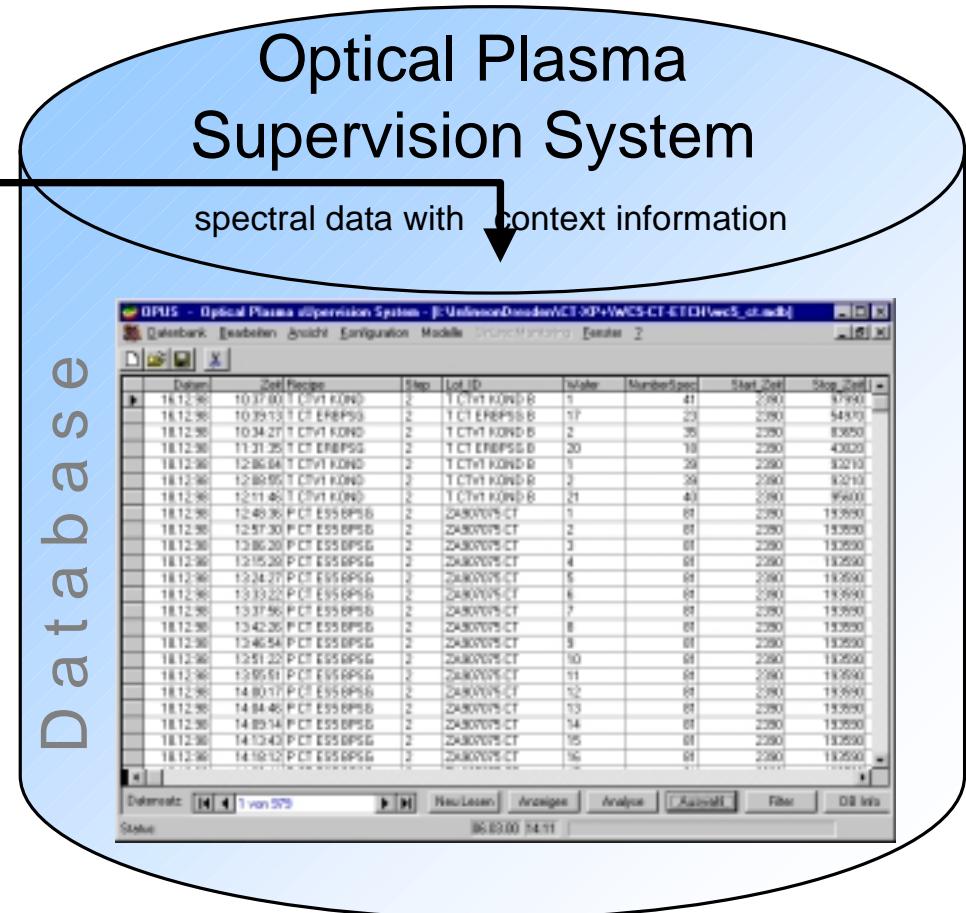
- spectral range: 200 - 950 nm
- resolution: < 2 nm
- CCD line channels: 1024
- connection to Host PC via TCP-IP, RS 232
- internal memory for 2500 spectra
- internal data processing for endpoint detection; up to 100 endpoint script's are available
- digital/analog port's for connection to Etch-Tool



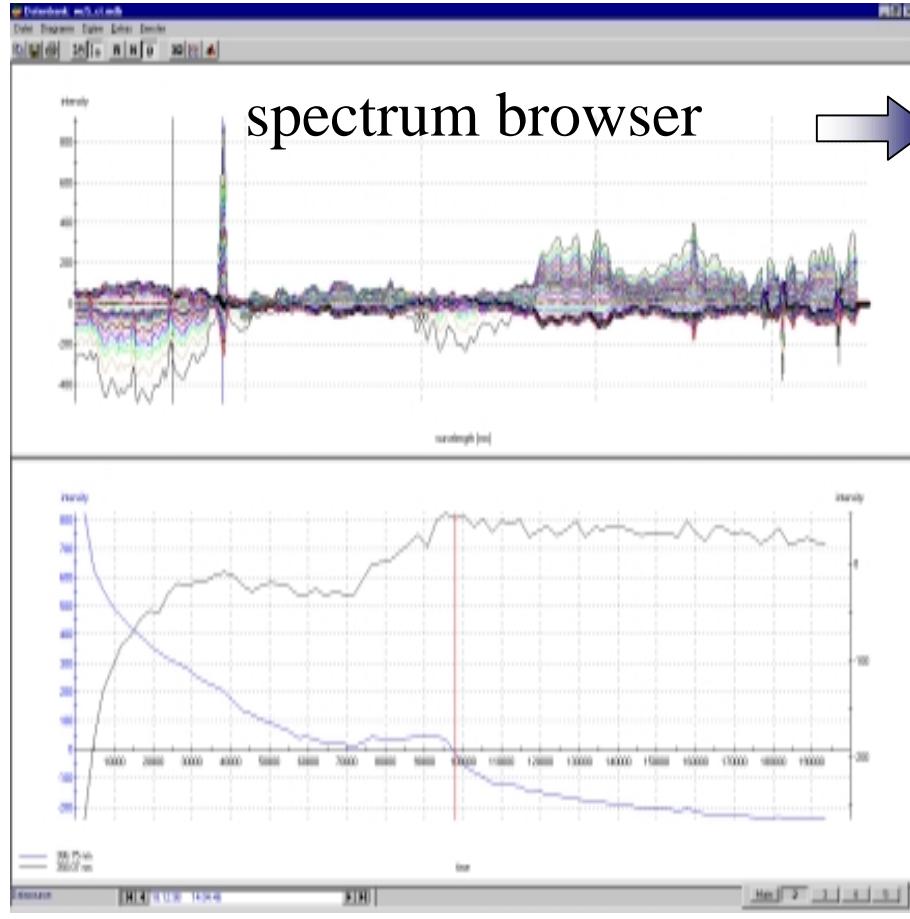
Acquisition of spectra in a database

measurement component

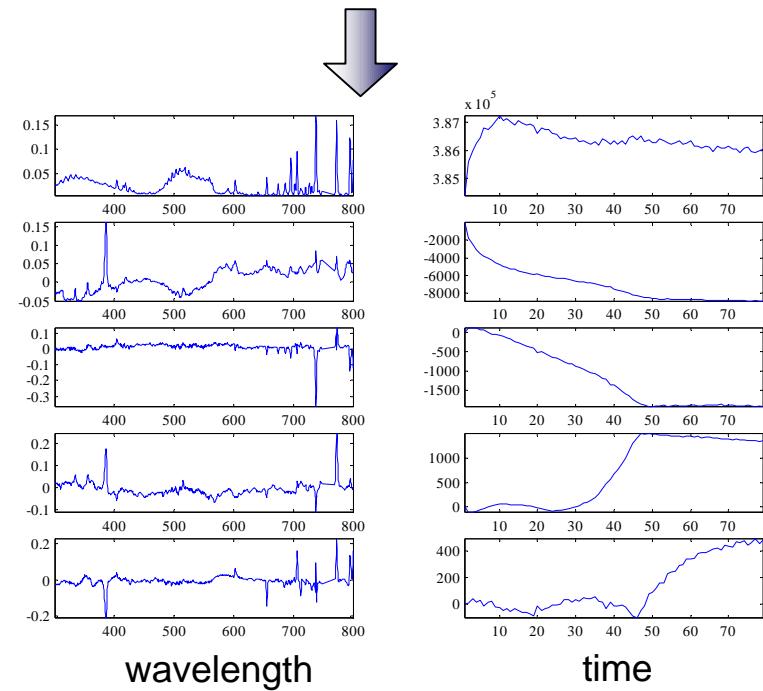
- manual
- automatic by optical trigger
- automatic by tool communication (TICS, EQM, SECS)



Spectra simple view



decomposition of measured data into main spectral and time-related components



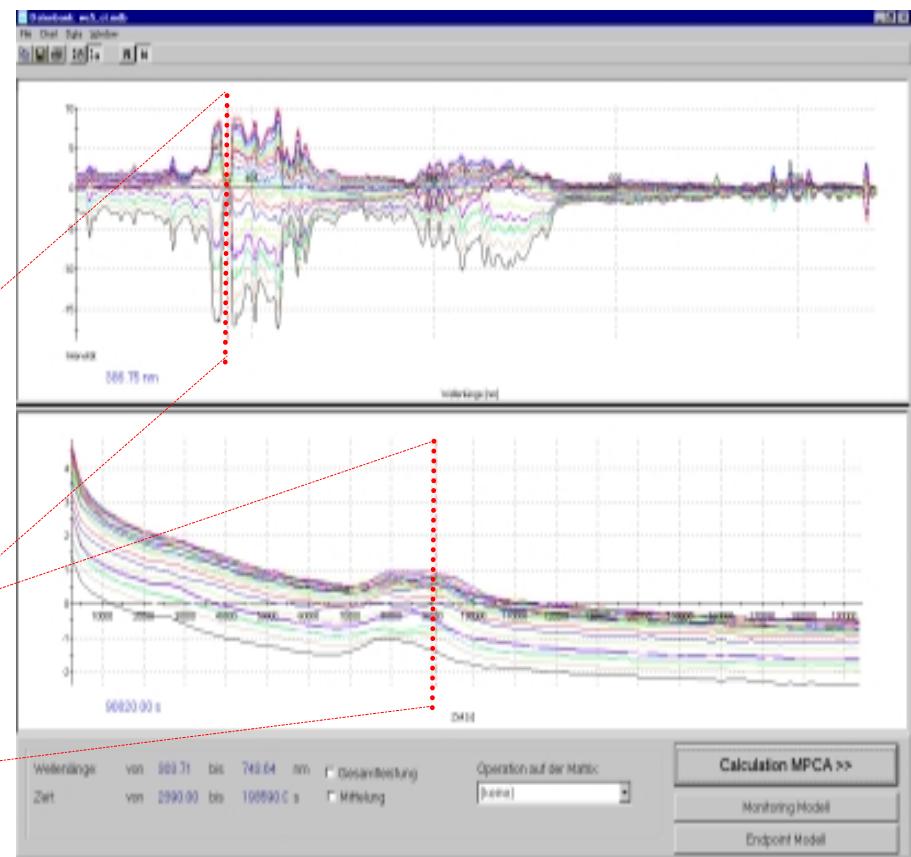
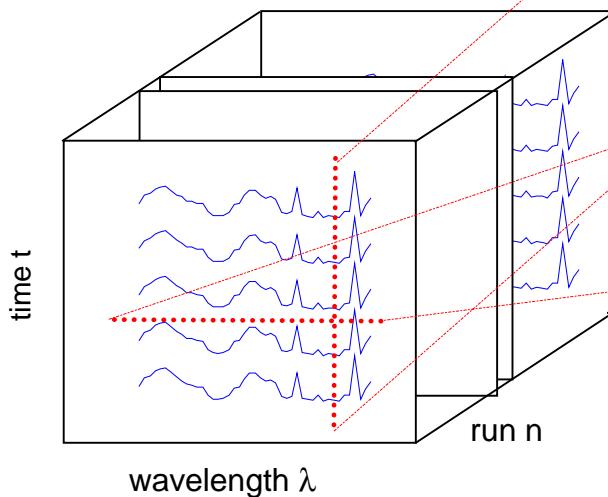
Database Viewer

data acquisition

- SQL based selection of etch-steps
- time and wave range extraction by zooming



data block $\Lambda \in \mathbb{R}^{\lambda \times t \times n}$

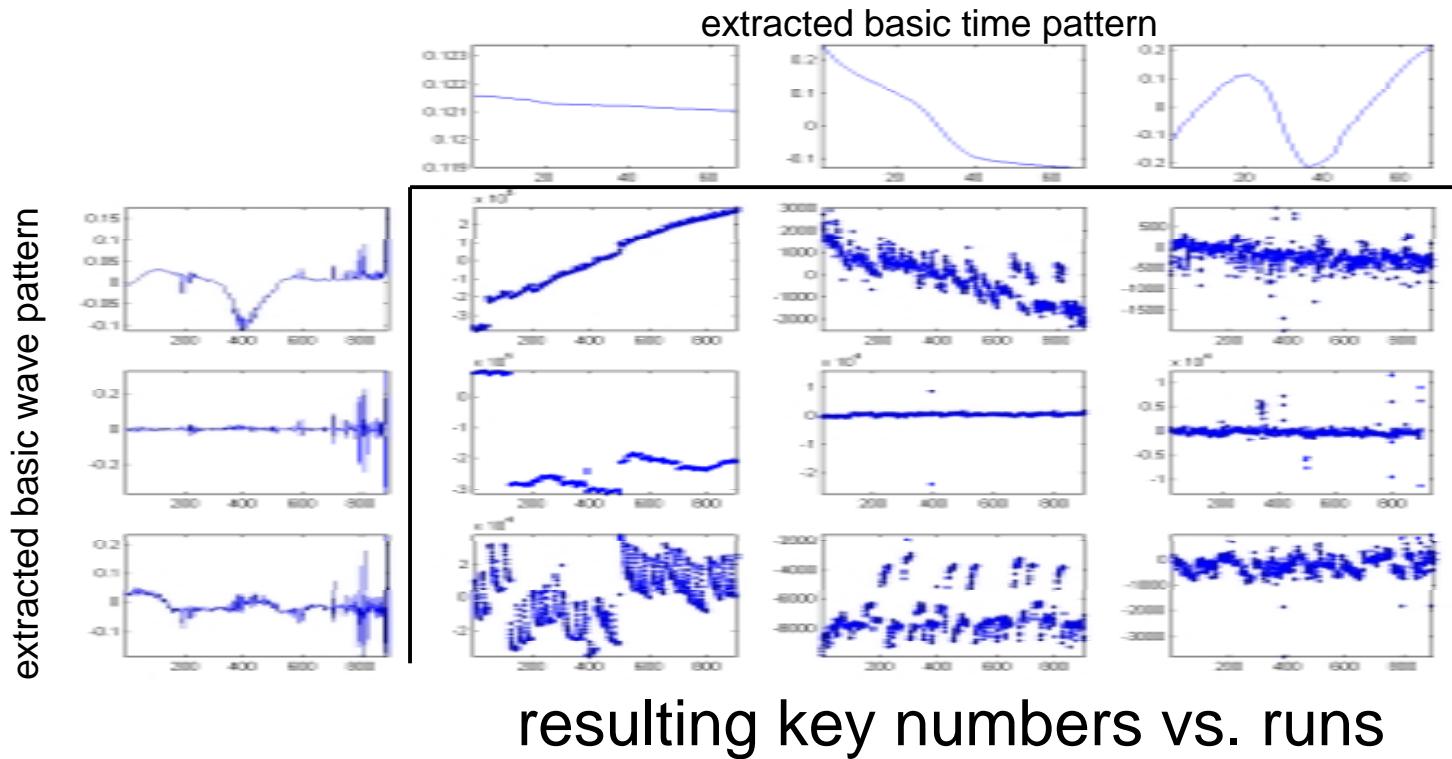


visualization of spectra and time behavior of selected runs

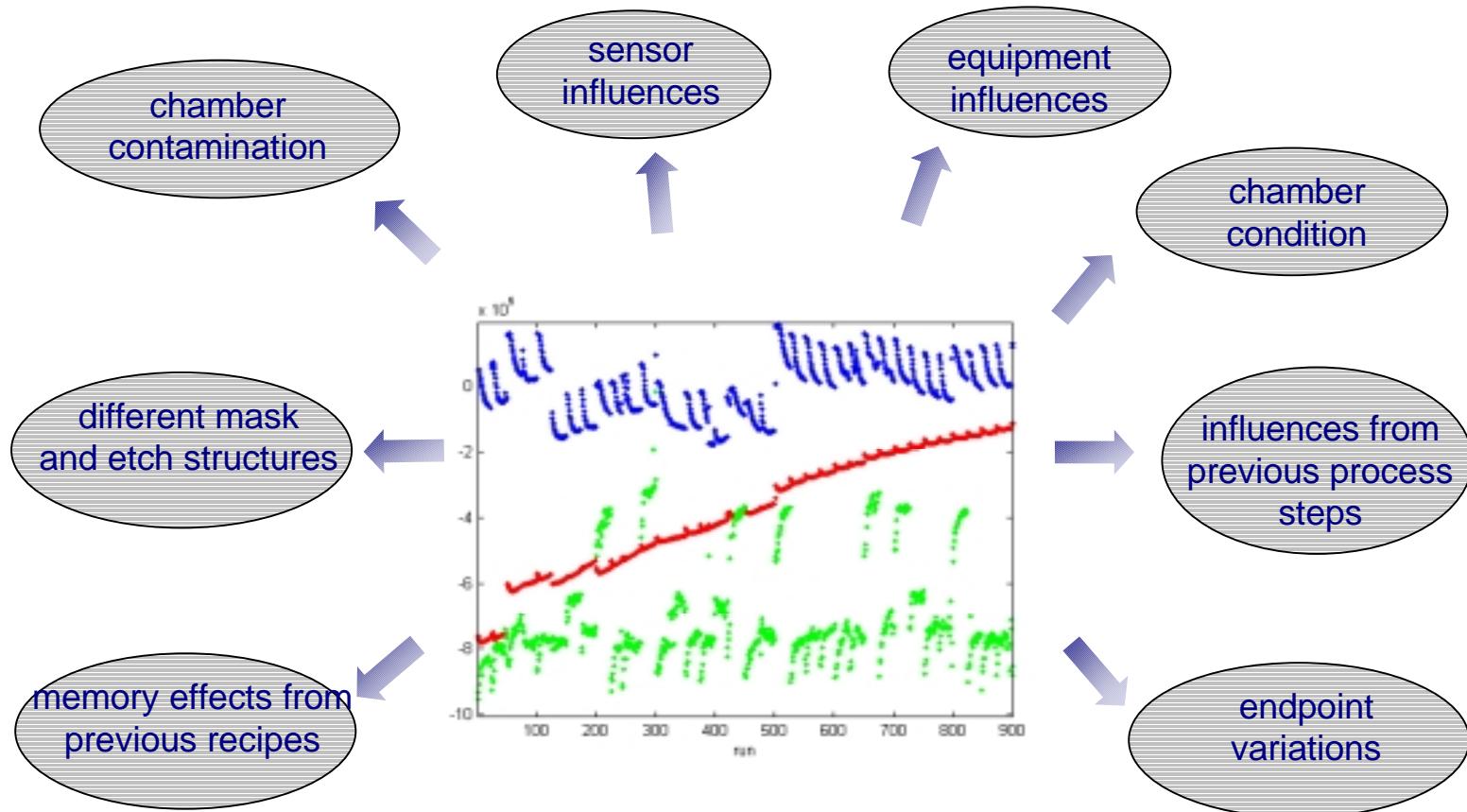


Multi-Way statistical analysis for process monitoring

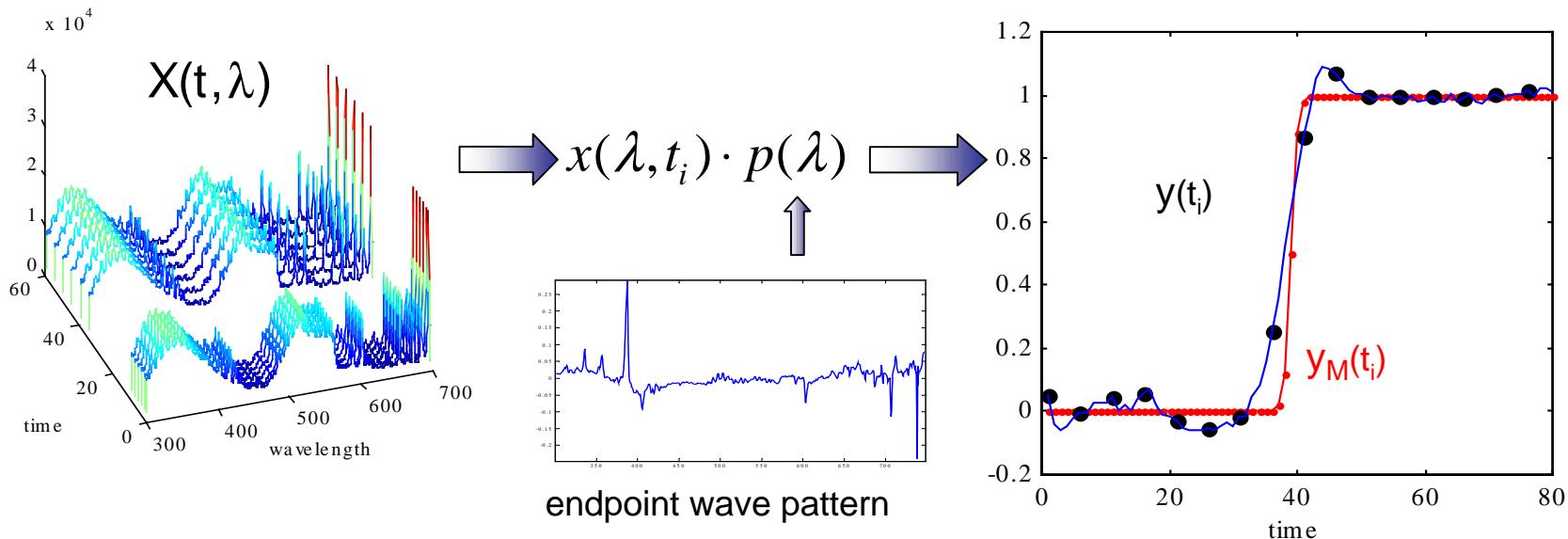
→ extraction of significant process related key numbers



separated effects from spectral data



Synthesis of an optimal endpoint signal



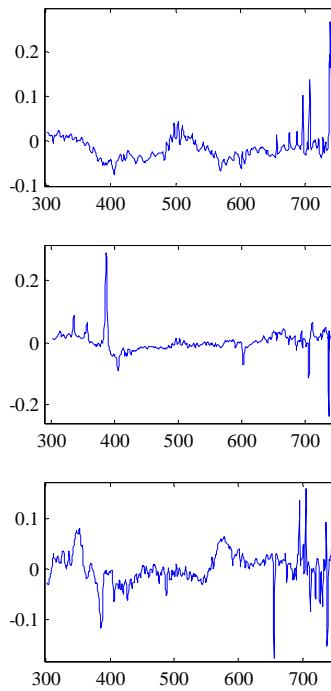
objective:

→ generation of suitable wave pattern which yields to sensitive and long-term robust endpoint signals

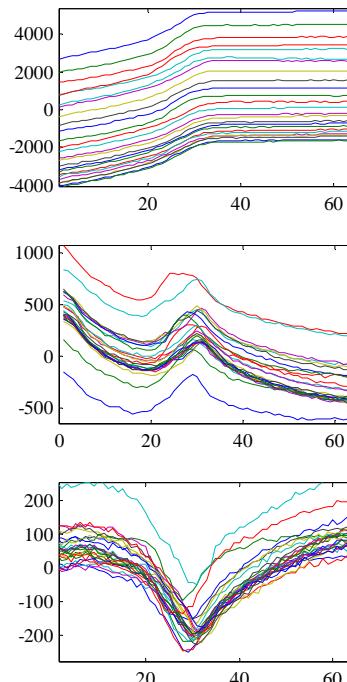


Decomposition of several runs for endpoint synthesis

decomposed
wave components



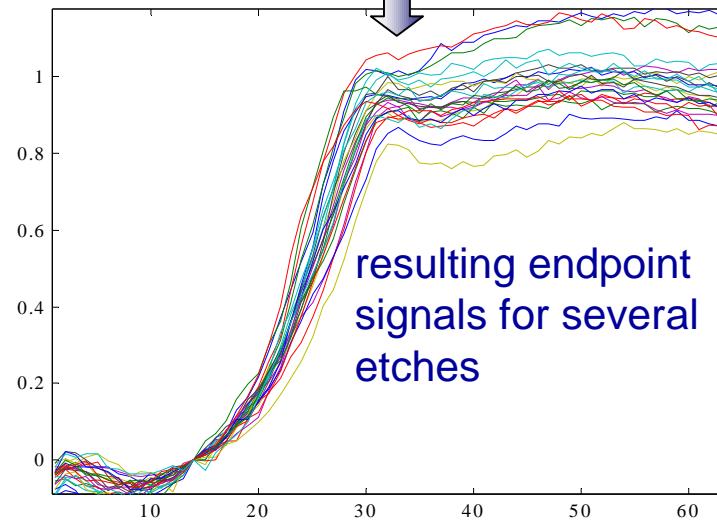
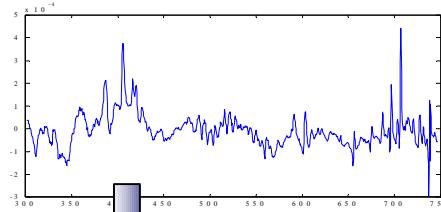
resulting time signal
for several etches



suitable
superposition



resulting endpoint wave
pattern



resulting endpoint
signals for several
etches



Summary

- Integration of MPM spectrometer within FAB-IT-Infrastructure for automatic measurement at etch tools
- Development of multiway statistical methods for extraction of key numbers associated with characteristic equipment and process features
- Synthesis of sensitive and robust endpoint signals by selecting a suitable superposition of the dynamics of each spectral channel

